## Vivekanand College, Kolhapur (Autonomous)

## Department of Electronics

B. Sc-III, Sem-VI Paper Code: (DSC 1005F2)

Paper Name: Power Electronics

**Intermal Examination Notice** 

Date: 16/06/2021

This is to inform all the student of B. Sc.-III class, we are conducting **internal examination** for 20 marks **on 21/06/2021** using **Google platform**. The Google form link will be sent on what's app group 5 min before commencement of the exam. The detail time schedule of online test is given below.

Date	Time	Mode
21/06/2021	11.30 am-12.30 pm	Online-Google Platform

Subject teacher

Mr. P. R. Bagade



## Power Electronics-Internal Exam-Sem VI-2021

	aper No-VI Section-I & II	Subject Code: DSC-1005F2
	ame of Paper: Power Electronics	
	ata: 21/06/2021 Time:11.30 pm to 12 otal Marks: 20	2.30 pm
	otal Marks: 20	
	.All Questions are compulsory.	
	.Each Question carries 1 Marks.	
3	Figure to write indicate full marks.	
* In	dicates required question	
1.	Email *	
2.	Name of the student (First Name Middl	e Name Last Name) *
3.	Roll number *	
	LINE IS	
4.	1) A p-n junction diode is as	switching device.
	Mark only one oval.	
	Unidirectional	
	Bi-directional	
	Multidirectional	
	none of the above	1.402040



	Mark only one oval.
	☐ Infinity
	large
	very large
	small
6.	3) The process of conductivity modulation results in
	Mark only one oval.
	Increase in the switching frequency
	Increase in the on state loss
	Increase in the breakdown voltage.
	Reduction in on state loss
7.	4) Which of the following device has the terminals collector, emitter, gate  Mark only one oval.  BJT
	MOSFET
	☐ IGBT
	SCR
8.	5) is the Power semiconductor device having highest switching speed.
	Mark only one oval.
	BJT
	MOSFET
	☐ IGBT
	None of these  IGBT  Strangen of these  Strangen of these

5. 2) Power transistors have relatively ----- current gain ( $\beta$ ).

9.	6) IGBT stands for	
	Mark only one oval.	
	Insulated gate bidirectional transistor	
	Inductive gate bipolar transistor	
	Insulated gate bipolar transistor	
	Inductive gate bidirectional transistor	
10.	7) In BJT, switching loss is occurs	
	Mark only one oval.	
	Only at turn ON	
	Only at turn OFF	
	Both at turn ON-OFF	
	none of the above	
11.	8) is the type of Power Transistor.	
	Mark only one oval.	
	BJTs	
	MOSFETs	
	☐ IGBTs	
	All of the above	
12.	9) Power MOSFET is controlled device.	
	Mark only one oval.	
	Current	
	Voltage	
	Magnetic field	ESTD.
	None of the above	ESTD.

13.	10) The Gate terminal of a MOSFET is isolated from the semiconductor by a thin layer of
	Mark only one oval.
	ZnO
	Si02
	Polymer
	None of these

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Google Forms



## Vivekanand College, Kolhapur (Autonomous)

B.Sc.-III (Sem-IV)

Paper Code: DSC 1005F2

Paper Name : Power Electronics Internal Exam- 2020-21 Marksheet

Sr. No	Timestamp	Name of the student	Marks Outoff 20
1	21-06-2021 10:58	Shreyas Sunil Powar	8
2	21-06-2021 11:14	Durga vaijanath yadav	14
3	21-06-2021 11:16	Snehal mohan chougule	14
4	21-06-2021 11:17	Shrutika sudhir gujar	10
5	21-06-2021 11:17	Gauri Rahul Bedagkar	10
6	21-06-2021 11:22	KUNAL KETAN SARNAIK	14
7	21-06-2021 11:26	Siddhesh shivaji shinde	10
8	21-06-2021 11:27	Aakash Rajencdra Kalgutar	14
9	21-06-2021 11:28	Malhar Uday Mane	20
10	21-06-2021 11:29	Siddharth shital shete	14
11	21-06-2021 11:29	Sunil Uttam Ghorpade	2
12	21-06-2021 11:29	Ashish kamble	12
13	21-06-2021 11:30	Vilas Bharmanna Dandgule	14
14	21-06-2021 11:32	Bharat Shivaji Shinagare	16
15	04-08-2021 13:39	Karan M Gharale	12
16	04-08-2021 14:31	Dipak Vishwanath Sutar	14
17	04-08-2021 16:39	dipaksutar@gmail.com	10

Sign of Teacher
Mr.P.R.Bagade

